

## Product Features

- High power RF amplifier
- Solid State power amplifier
- High linearity and high efficiency
- 50 ohms input / output impedance
- Doherty amplifier design

## Application

- LTE Repeater



LTE Multi Carrier RF Amplifier

## Electrical Specification

Parameter	Specification	Remark
Frequency Range	2620MHz~2690MHz	70MHz BW
Output Power	40W (+46dBm)	
Gain	53dB±1dB	
Gain Flatness	1dB peak to peak	
ACLR (WCDMA 2FA)	±5MHz < -32dBc ±10MHz < -32dBc	RBW 30kHz
Input VSWR	1.5:1 max.	
Output VSWR	1.5:1 max.	
DC Current Consumption	+27V 8A max.	
Enable	TTL Low Active	
Output Detect	+3.0V @Po=40W	0.1V/dB

## Environmental Specification

Parameter	Specification	Remark
Operating Temperature	-20°C ~ +60°C	
Storage Temperature	-30°C ~ +85°C	
Relative Humidity	0%~90%	Non-condensing



## Mechanical Specification

Physical Dimension : 150mm X 105mm X 25mm

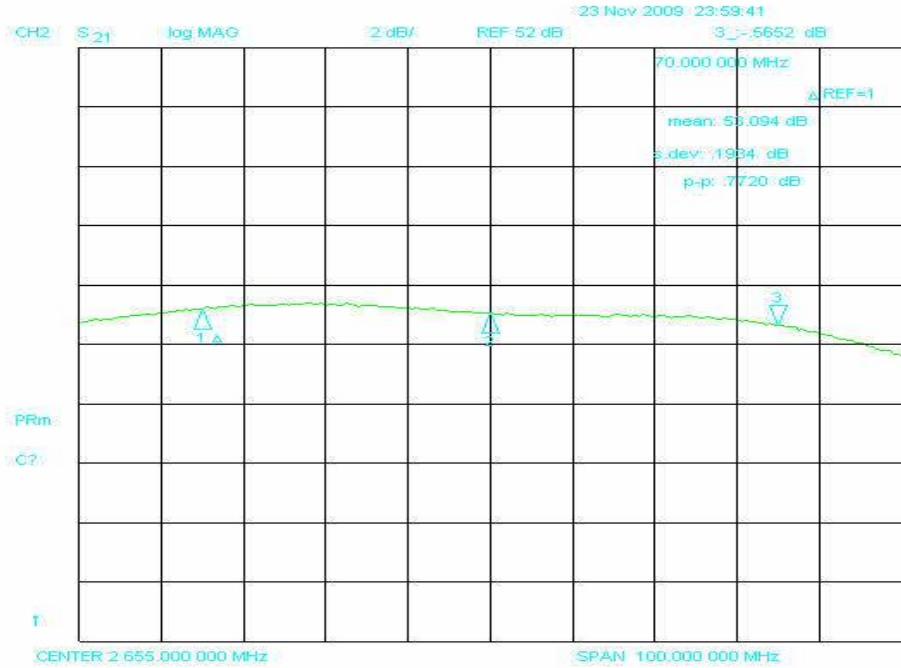
## Pin Assignment

I/O Interface (D-Sub 9Pin Male)	1. Enable/Disable	TTL Low
	2,3,6 VCC	+27V
	4. Over Power Alarm	Po=+48dBm Over
	5. VSWR Alarm	Po=+36dBm Open
	7. Power Monitor	3.0V@Po=+46dBm
	8,9. GND	



## Electrical Test Data

Gain & Flatness



ACLR@ Po=40W

